CLAIMS

1. A method for fabricating a magnetic head comprising the steps of:

fabricating a write head portion of said magnetic head, including the steps of:

fabricating first magnetic pole;

fabricating an insulation layer above said first magnetic pole;

depositing a seed layer upon said insulation layer;

electroplating an induction coil upon said seed layer;

removing portions of said seed layer that are not covered by said induction coil, utilizing a RIE process;

wherein said RIE process utilizes fluorine species, and said seed layer is comprised of a material that forms a gaseous compound with said fluorine species.

2. A method for fabricating a magnetic head as described in claim 1 wherein said seed layer is comprised of a material selected from the group consisting of tungsten and titanium.

3. A method for fabricating a magnetic head as described in claim 2 wherein said seed layer has a thickness of approximately 500 Å to 800 Å..

4. A method for fabricating a magnetic head as described in claim 2 wherein said seed layer is fabricated in a sputter deposition process.

5. A method for fabricating a magnetic head as described in claim 2 wherein said RIE process utilizes a compound selected from the group consisting of CF_4, CHF_3, SF_6, C_2F_6 and C_3F_8 to provide said fluorine ion species.

6. A method for fabricating a magnetic head as described in claim 1 wherein said induction coil is composed of copper, and wherein said seed layer includes and an upper part comprised of copper and a lower portion comprised of a material selected from the group consisting of tungsten, titanium and tantalum, and wherein said induction coil is electroplated upon said copper upper portion of said seed layer.

7. A method for fabricating a magnetic head comprising the steps of:

fabricating a write head portion of said magnetic head, including the steps of:

fabricating a first magnetic pole;

fabricating a seed layer above said first magnetic pole;

electroplating a second magnetic pole upon said seed layer;

removing portions of said seed layer that are not covered by said second magnetic pole utilizing a RIE process;

wherein said RIE process utilizes fluorine ion species, and said seedlayer is comprised of a material that forms a gaseous compound with said fluorine ion species.

8. A method for fabricating a magnetic head as described in claim 7 wherein said seed layer is comprised of a material selected from the group consisting of tungsten and titanium.

9. A method for fabricating a magnetic head as described in claim 8 wherein said seed layer has a thickness of approximately 500 Å to 800 Å.

10. A method for fabricating a magnetic head as described in claim 8 wherein said seed layer is fabricated in a sputter deposition process.

11. A method for fabricating a magnetic head as described in claim 7 wherein said RIE process utilizes a compound selected from the group consisting of CF_4, CHF_3, SF_6, C_2F_6 and C_3F_8 to provide said fluorine ion species.

12. A method for fabricating a magnetic head as described in claim 7 wherein said second magnetic pole is composed of NiFe, and wherein said seed layer is fabricated to include an upper part comprised of NiFe and a lower part comprised of a material selected from the group consisting of tungsten, titanium and tantalum, and wherein said second magnetic pole is electroplated upon said NiFe upper portion of said seed layer.

13. A method for fabricating a magnetic head as described in claim 7 wherein said seed layer is fabricated upon said first magnetic pole.

14 A method for fabricating a magnetic head as described in claim 13 wherein said seed layer is a write gap layer disposed between said first magnetic pole and said second magnetic pole.

15. A magnetic head comprising:

a write head portion,

an insulation layer being disposed within said write head portion;

a seed layer being disposed upon said insulation layer,

an induction coil being disposed upon said insulation layer;

said seed layer being comprised of a material selected from the group consisting of tungsten, tantalum and titanium.

16. A magnetic head as described in claim 15 wherein said seed layer is formed with a thickness of approximately 500 Å to 800 Å.

17. A magnetic head as described in claim 15 wherein said induction coil is comprised of copper, and wherein said seed layer is comprised of a lower part and a copper upper part, wherein said lower part is disposed upon said insulation layer, and said induction coil is disposed upon said copper part.

18. A magnetic head as described in claim 17 wherein said lower part of said seed layer is formed with a thickness of approximately 500 Å to 800 Å, and said copper part of said seed layer is formed with a thickness of approximately 100 Å.

19. A magnetic head comprising:

a write head portion including a first magnetic pole and a second magnetic pole;

a seed layer being disposed between said first magnetic pole and said second magnetic pole, said second magnetic pole being disposed upon said seed layer;

said seed layer being comprised of a material selected from the group consisting of tungsten, tantalum and titanium.

20. A magnetic head as described in claim 19 wherein said seed layer is formed with a thickness of approximately 500 Å to 2,000 Å.

21. A magnetic head as described in claim 19 wherein said second magnetic pole is comprised of an NiFe, and wherein said seed layer includes a lower part and an upper part comprised of NiFe, and wherein said second magnetic pole is disposed upon said NiFe upper part of said seed layer.

22. A magnetic head as described in claim 21 wherein said NiFe upper part of said seed layer is formed with a thickness of approximately 100 Å, and said lower part of said seed layer is formed with a thickness of approximately 500 Å to 2,000 Å.

23. A hard disk drive comprising:

at least one hard disk being adapted for rotary motion upon a disk drive;

at least one magnetic head being adapted to fly over said hard disk for writing data on said hard disk, said magnetic head including:

a write head portion,

an insulation layer being disposed within said write head portion;

a seed layer being disposed upon said insulation layer,

an induction coil being disposed upon said insulation layer;

said seed layer being comprised of a material selected from the group consisting of tungsten, tantalum and titanium.

24. A hard disk drive as described in claim 23 wherein said seed layer is formed with a thickness of approximately 500 Å to 800 Å.

25. A hard disk drive as described in claim 23 wherein said induction coil is comprised of copper, and wherein said seed layer is comprised of a copper part and a lower part, wherein said lower part is disposed upon said insulation layer, and said induction coil is disposed upon said copper part.

26. A hard disk drive as described in claim 25 wherein said lower part of said seed layer is formed with a thickness of approximately 500 Å to 800 Å, and said copper part of said seed layer is formed with a thickness of approximately 100 Å.

27. A hard disk drive comprising:

at least one hard disk being adapted for rotary motion upon a disk drive;

at least one magnetic head being adapted to fly over said hard disk for writing data on said hard disk, said magnetic head including:

a write head portion including a first magnetic pole and a second magnetic pole;

a seed layer being disposed between said first magnetic pole and said second magnetic pole, said second magnetic pole being disposed upon said seed layer;

said seed layer being comprised of a material selected from the group consisting of tungsten, tantalum and titanium.

28. A hard disk drive as described in claim 27 wherein said seed layer is formed with a thickness of approximately 500 Å to 2,000 Å.

29. A hard disk drive as described in claim 27 wherein said second magnetic pole is comprised of an NiFe, and wherein said seed layer includes a lower part and an upper part comprised of NiFe, and wherein said second magnetic pole is disposed upon said NiFe upper part of said seed layer.

30. A hard disk drive as described in claim 29 wherein said NiFe upper part of said seed layer is formed with a thickness of approximately 100 Å, and said lower part of said seed layer is formed with a thickness of approximately 500 Å to 2,000 Å.